		U.S. Department ent and Trademark	~~	Attorney Docket Number 5308-156			Serial No. 09/911,995			
Patent and Trademark Office 5308-156 Applicants: Ryu et al. Filing Date: July 24, 2001										
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			U. S	. PATENT DO	CUMENTS					
Examiner Initial		Document Number	Date	И	ame Class		Subclass	Filing Date if Appropriate		
272	1.	5,587,870	12/24/96	Anderson et a	d.	361	313			
	2.	5,877,045	3/2/99	Kapoor		438	151			
	3.	6,136,728	10/24/00	Wang		438	773	·		
	4.	6,063,698	05/16/00	Tseng et al.		438	585			
1	5.	6,048,766	04/11/00	Gardner et al		438	257			
271%	6.	6,028,012	02/22/00	Wang		438	779			
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		•	FORE	GN PATENT	DOCUMENTS					
		Document Number	Date	Co	untry	Class	Subclass	Translation Yes No		
27/1/2	7.	WO99/63591	12/09/99	PCT						
なれられ	8.	WO00/13236	03/09/00	PCT						
		OTHER DOO	CUMENTS (I	ncluding Autho	r. Title, Date, Pe	ertinent Pages	, Etc.)			
ARK	9.	OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.) Mutin, P. Herbert, "Control of the Composition and Structure of Silicon Oxycarbide and Oxynitride Glasses Derived from Polysiloxane Precursors," Journal of Sol-Gel Science and Technology. Vol. 14 (1999) pp. 27-38.								
SIRK	10.	del Prado et al. "Full Composition Range Silicon Oxynitride Films Deposited by ECR-PECVD at Room Temperatures," Thin Solid Films. Vol. 343-344 (1999) p. 437-440.								
STATA	11.	 Wang et al. "High Temperature Characteristics of High-Quality SiC MIS Capacitors with O/N/O Gate Dielectric," IEEE Transactions on Electron Devices. Vol. 47, No. 2, February 2000. 								

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G. MUNSON DATE CONSIDERED 3 Mou-ch 2003

Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO		U.S. Department (Attorney Docket Number 5308-156			Serial No. 09/911,995				
LIST	OF DO	OCUMENTS CITE	D BY APPLI	CANT							
OIP.	ED	se several sheets if	necessary)				·				
	• ••••			Applicants: Ryu et al.							
JAH TENER	- 2001			Filing Date: July 24, 2001			Group 2811				
PA	ALARY	,	U. S	. PATENT DO	CUMENTS		_				
Examiner Initial		Document Number	Date	Name		Class	Subclass	Filing Date if Appropriate			
genop	1	5,479,316	12/26/95	Smrtic et al.		361	322				
	2	5,739,564	04/14/98	Kosa et al.		257	298				
	3	6,228,720	05/08/01	Kitabatake et al.		438	268				
3	4	6,239,463	05/29/01	Williams et al.		257	328				
ق	5	6,316,791	11/13/01	Schörner et al.		257	77				
1	6	6,593,620	07/15/03	Hshieh et al.		257	335				
27hM	7	6,610,366	08/26/03	Lipkin		427	378				
			FORE	IGN PATENT	DOCUMENTS			<u>'</u>			
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LIMA	9	Dimitrijev et al., "Nitridation of Silicon-Dioxide Films Grown on 6H Silicon Carbide", IEEE Electronic Device Letters, Vol. 18, No. 5, May 05, 1997, pp. 175-177.									
1	10	De Mao et al., "Thermal Oxidation of SiC in N2O", J. Electrochem. Soc., Vol. 141, 1994, pp. L150-L152.									
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